SRAM Architecture with A Full-Swing Local Bitline Based on the 22-nm Fin FET Technology

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Abstract: *In this paper, the drawback of the average-8T SRAM architecture based on an advanced technology is analyzed, and a suitable SRAM architecture that overcomes this drawback is proposed. However, in the case of anaverage-8T SRAM based on an advanced technology, such as a 22-nm FinFET technology, where the variation in threshold voltage is large, the boosted WL voltage cannot be used, because it degrades the read stability of the SRAM. Thus, a full-swing local BL cannot be achieved, and the gate of the read buffer cannot be driven by the full supply voltage (VDD), resulting in a considerably large read delay. To overcome the above disadvantage, in this paper, a differential SRAM architecture with a full-swing local BL is proposed. In the proposed SRAM architecture, full swing of the local BL is ensured by the use of cross-coupled pMOSs, and the gate of the read buffer is driven by a fullVDD, without the need for the boosted WL voltage. Various configurations of the proposed SRAM architecture, which stores multiple bits, are analyzed in terms of the minimum operating voltage and area per bit. It should be noted that the proposed differential SRAM architecture can resolve the half-select issue without the need for a write-back scheme, and it exhibits a competitive area; it also exhibits a full-swing local bitline (BL) that enables a considerably smaller read delay than that of average-8T SRAM architecture.*

Keywords: Bit-interleaving, FinFET, low-voltage operation, static random access memory (SRAM)..

I. eINTRODUCTION

From last 5 decades we are scaling down CMOS devices to achieve the better performance in term of speed power dissipation ,size and reliability .Variability has become increasingly troubling as the SRAM cell size is reduced ,such as short channel effect ,higher DIBL, poor sub threshold swing collectively known as SCE.

While technology scaling has made it possible to put more and more transistors on to a simple chip while at the same time allowing them to run ever faster, less simple effects are starting to show. Continuously shrinking of the device size comes with serious constraint on memory design like power consumption and stability. The device variation and leakage are increasing as the miniaturization of the transistor continues which also affects the reliability and performance of the device. Scaling of MOSFET dimensions and power supply imposes.

The Fin type MOSFET(FinFET)is one of the most desired device to scaled CMOS device. To solve this problem 3-D device structure could be a solution . In the FinFET short channel effects are suppressed by a thin body instead of channel dopants.

The 8T FinFET SRAM is shown in fig 2 . the 8T SRAM is similar to 6T with addional 2 transistors to decoupled separate read and write operation . in 6T SRAM during read operation there is potential stability problem . To overcome the problem of data storage destruction during the read operation an 8T SRAM is implemented, for which separate read/write line are used.

Over the years, the 8T SRAM cell [Fig.2] was the de facto choice for SRAM design . the need for bigger memory devices is always present , it is crucial importance that this cell is scaled to minimum dimensions. However, some constraints have to be satisfied. For proper dimensioning of the cell, two basic constraints have to be satisfied. Pull Up transistors have

to be weaker than Pass Gate transistors (this constraint is called write ability), and pull down (PD) transistors have to be stronger than Pass Gate transistors (readability). A write operation in SRAM is typically carried out at a WL voltage of VDD. In some cases, WL voltage can be lowered during the cell. In this paper 8T FinFET SRAM cell design and read/write operation has been studies using Visual TCAD simulation

Fig. 2. (a) Average-8T SRAM architecture and (b) its operational waveform.

II. RELATED WORK

"Reduction of leakage power in 8T SRAM cell using virtual ground," This paper describes stability problems in 6T SRAM cell and their solutions with 8T SRAM cell. 8T SRAM with the virtual ground concept has been proposed which reduces leakage power. Comparison of 8T SRAM cell proposed with conventional 6T SRAM cell with respect to leakage power are proved by simulation and experimentally using the tool cadence (180nm technology).

"Design and Verification of Low Power SRAM using 8T SRAM Cell Approach," SRAM cell stability will be a

primary concern for future technologies due to variability and decreasing power supply voltages. Advances in chip designing have made possible the design of chips at high integration and fast performance. Lowering power consumption and increasing noise margin have become two central topics in every state of SRAM designs.The Conventional 6T SRAM cell is very much prone to noise during read operation. To overcome the read SNM problem in 6T SRAM cell, researchers have considered different configurations for SRAM cells such as 8T, 9T, 10T etc. bitcell design. These designs can improve the cell stability but suffer from bitline leakage noise. This paper targets reduction of power consumption and evaluates the static noise margin of 8T SRAM bitcells. In this paper, we propose a novel 8T SRAM topology that achieves both cell stability and also reduces Power Consumption. With the proposed 8T SRAM circuit, the Read Static Noise Margin is nearly twice that of the Conventional 6T SRAM Cell.

"A 5.61 pJ, 16 kb 9T SRAM with Single-ended Equalized Bitlines and Fast Local Write-back for Cell Stability Improvement," A 5.61 pJ, 16 kb 9T SRAM is implemented in 65nm CMOS technology. A single-ended equalized bitline scheme is proposed to improve both read bitline voltage swing and sensing timing window. A fast local write-back allows the half-select-free write operation without performance degradation. The test chip shows a minimum operating voltage of 0.24V and a minimum energy of 5.61pJ at 0.3V.

"A Sub-Threshold 8T SRAM Macro with 12.29 nW/KB Standby Power and 6.24 pJ/access for Battery-Less IoT SoCs," We present an ultra-low power (ULP) 1 KB SRAM macro for Internet of Things (IoT) battery-less systems-on-chip (SoCs) operating under varying energy harvesting conditions. The unique combination of features within this array allows battery-less SoCs to retain important information for a significantly longer period of time when energy harvesting conditions are poor. The array uses 8T high-threshold (high-VT) static random access memory (SRAM) cells with word line boosting to eliminate write failures coupled with a read-before-write scheme to address read-disturb in half-selected cells. Due to the reduced on current in high-VT devices, read word line boosting is implemented to improve the drive

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strength of the read buffer, and to eliminate read failures. Leakage currents through the unselected cells during a read operation is addressed by boosting the footer virtual VSS (VVSS) of the read port to the supply voltage (VDD). To reduce the power consumption of instruction memories in battery-less SoCs, two features were utilized in this array: a read burst mode is used when reading consecutive addresses to reduce the read energy, and instructions with higher percentages of "1" data are defined since reading a "1" is less costly than reading a "0" in 8T cells. The proposed array can operate at a wide range of supply voltages (350–700 mV) and has two ULP modes: standby with retention (1.5 pW/bit) and shutdown without retention (0.13 pW/bit). Aggressive power gating of all peripherals during the standby state reduces the array power consumption down to 12.29 nW/KB at 320 mV with data retention. Compared to previously published 8T arrays, the proposed design provides the lowest standby power. The complete shutdown of the array allows further reduction down to 1.09 nW/KB and is suitable for reducing the power consumption of data memories in battery-less SoCs. The measured results from a commercial 130 nm chip show that the proposed array consumes a minimum of 6.24 pJ/access with a 17.16 nW standby power at 400 mV. The read burst mode allows up to 22% reduction in energy/access at 400 mV.

III. EXISTING SYSTEM

Several SRAM cell alternatives with a decoupled read port have been proposed for a low-voltage operation. The advantage of adding a decoupled read port is that it eliminates the tradeoff between the read stability and the write ability in the SRAM array to which the bit-interleaving is not applied; thus, the read stability and write ability can be optimized separately, facilitating a low-voltage operation. An SRAM cell is also susceptible to soft errors induced by α-particles; to address these errors, it is necessary for the SRAM array to exhibit bit-interleaving. Fig. 3 shows a bit-interleaved SRAM array architecture. In a bit-interleaved SRAM array, the selected cells are the SRAM cells targeted for the read or write operation. The row half-selected cells are the

SRAM cells located on the selected row and the unselected column, whereas the column half-selected cells are the SRAM cells located on the unselected row and the selected column. During the write operation, the row half-selected cells are disturbed because of the selection of the wordline (WL) of the row half-selected cells. Thus, the stability of the row half-selected cells should also be considered in the SRAM design.
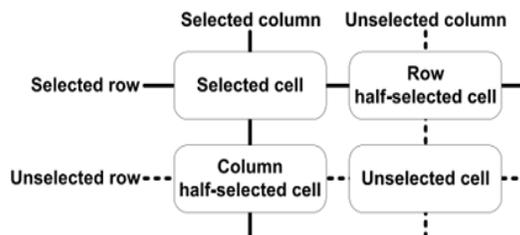
Figure 3: Selected, half-selected, and unselected cells in a bit-interleaved SRAM array

Disadvantages
Power consumption is high
Operating voltage is high

IV. Proposed System
The proposed differential SRAM stores 16 bits in one block, as in the case of an average-8T SRAM. Fig.4 shows the architecture of the proposed SRAM that stores i bits in one block. The minimum operating voltage and area per bit of the proposed SRAM depend on the number of bits in one block. The basic configuration of the proposed SRAM includes four cross-coupled inverter pairs, pass gate transistors (PGL1~4andPGR1~4), block mask transistors (MASK1 and MASK2), write access transistors (WR1 and WR2), read buffers (RD1 and RD2), a head switch (P1), and cross-coupled pMOSs (P2 and P3). The head switch and cross-coupled pMOSs of the proposed SRAM are notable differences from the average-8T SRAM. WLs (WL1~4), the block select signal (BLK), and the read WL (RWLB) are row-based signals, whereas the write WL (WWL), write BLs (WBL and WBLB), and read BLs (RBL and RBLB) are column-based signals.
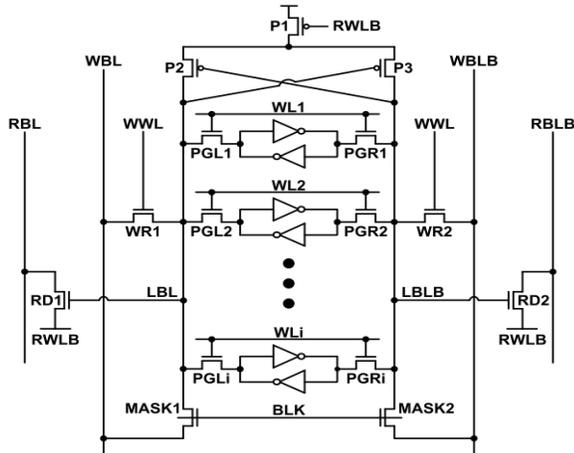
Fig. 4. Proposed SRAM architecture that stores i bits in one block

The architecture of the proposed SRAM is verified. The characteristics of this model are fitted to those of a commercial low-power device based on the 22-nm Fin FET technology. Table I lists the technology parameters. For a statistical analysis, it is assumed that the variation in Vth of each transistor follows a Gaussian distribution, whose standard deviation (σVth)is expressed by

$$\sigma_{V_{th}} = \frac{A_{Vt}}{\sqrt{Length \times Width}}$$
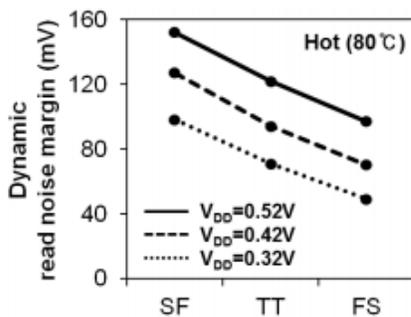
(a)
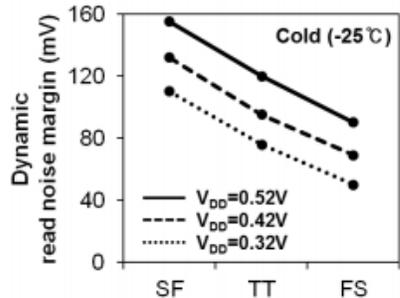
(b)

Fig. 7. Dynamic read noise margins of proposed SRAM at different PVT corners.

Read Operation

The read operation of the proposed SRAM architecture is described in Fig. 5(a). This operation is performed in two phases. During the first phase, BLK of the selected block is forced to remain at 0 V, and the selected WL is enabled. On the basis of the stored data, although the voltage of the LBL that is connected to the 1 storage node becomes high, its value cannot be as high as that of the full VDD because of the Vth drop through the pass gate transistor, and the voltage of the other LBL remains low. The read operation in the first phase is similar to that of the average-8T SRAM, except that the RBL is not discharged because the RWLB is high in the first phase. With the assertion of WL, although the 1 storage node is disturbed, the read disturbance is small because of the small capacitance at the LBL. This smaller read disturbance makes the proposed SRAM be able to operate in significantly lower operating voltage compared with 6T SRAM cell. The second phase starts with the falling of the RWLB. The assertion of the RWLB enables not only the discharge of the RBL but also the feedback of cross-coupled pMOSs. Positive feedback of the cross-coupled pMOSs increases the LBL to the value of the fullVDD, owing to which the LBL can achieve a full swing, and the gate of the read buffer is driven by the full VDD, without the need for a boosted WL voltage. Thus, in the case of the proposed SRAM based on an advanced technology, the suppressed WL voltage can be used to enhance the read stability, without degrading the read delay. In other words, the advantage of the proposed SRAM architecture is that it eliminates the tradeoff between the read stability and the read delay.
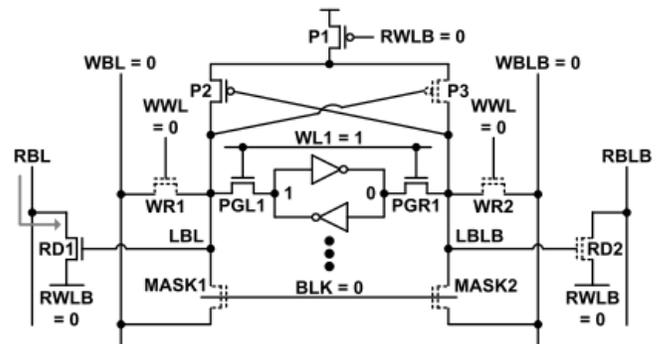
Fig 5(a). Read operation of SRAM architecture
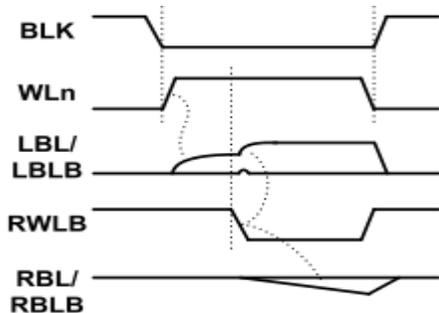
Fig 5(b). Read operational waveform of SRAM architecture.
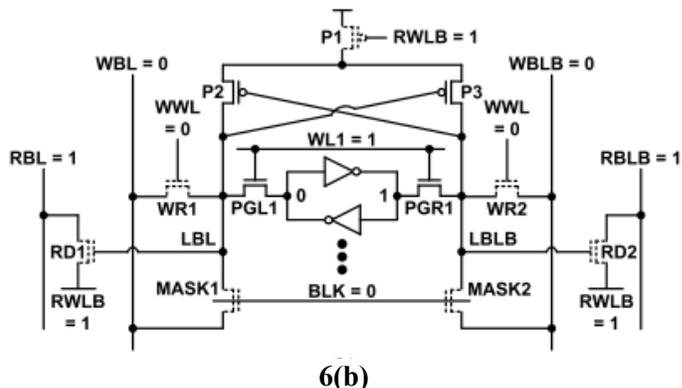
Write Operation

The write operation of the proposed SRAM architecture is shown in Fig. 6. As shown in this figure, BLK of the selected block is forced to remain at 0 V, and the selected WL is enabled. Further, the WWL is forced to remain at VDD so that the write access transistors are turned ON, and the WBLs are forced to remain at a certain voltage level on the basis of the write data. Both the storage nodes are connected to the WBLs through pass gate transistors and write access transistors. Thus, the write operation is differential, and the write ability of the proposed SRAM is better than that of the average-8T SRAM, whose write operation is single-ended.

6(b)

6(c)
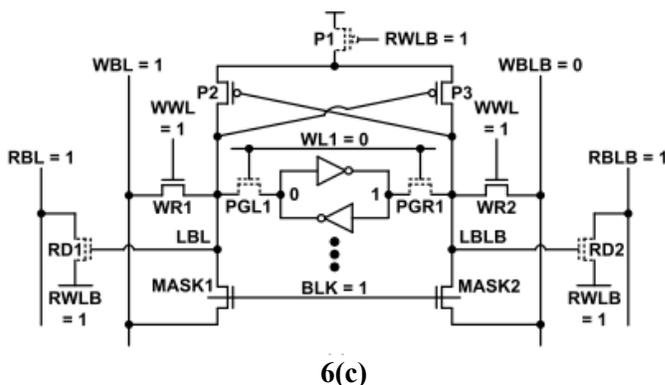
Fig. 6. (a) Selected, (b) row half-selected, and (c) column half-selected blocks of proposed SRAM architecture during write operation.
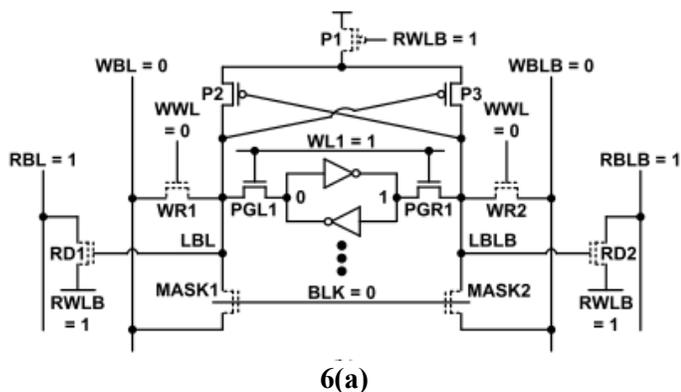
V. SIMULATION RESULTS

6(a)
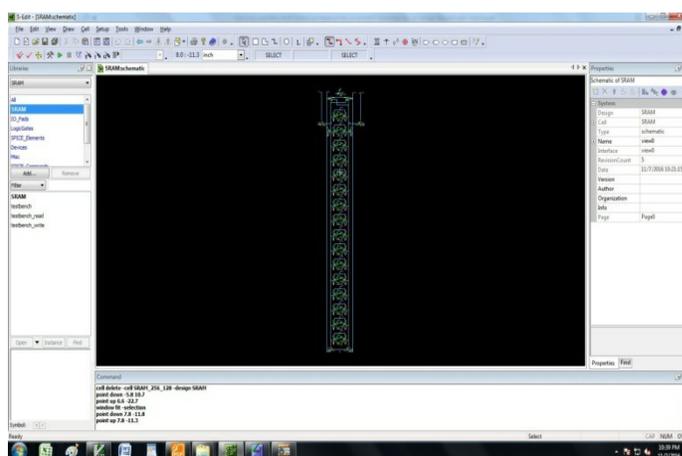
Figure 8: Overall architecture
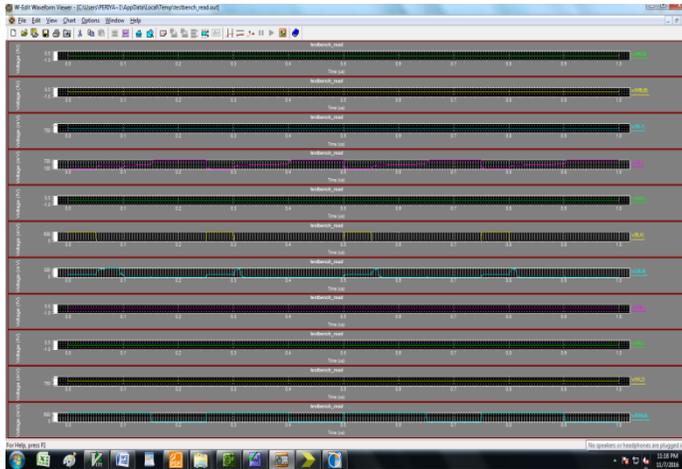
Figure 9: read operation
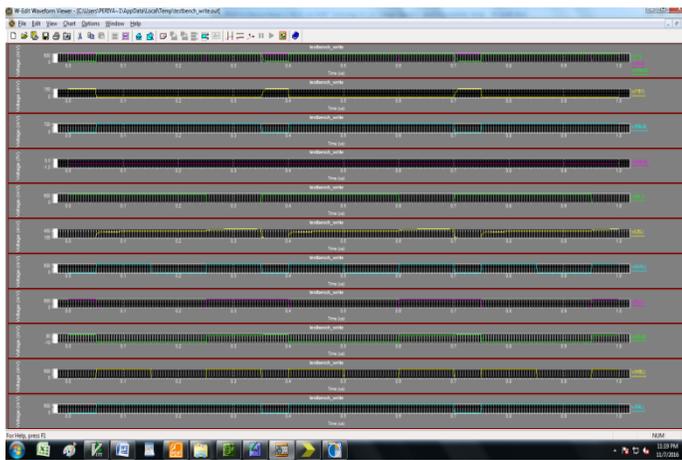
Figure 10: write operation
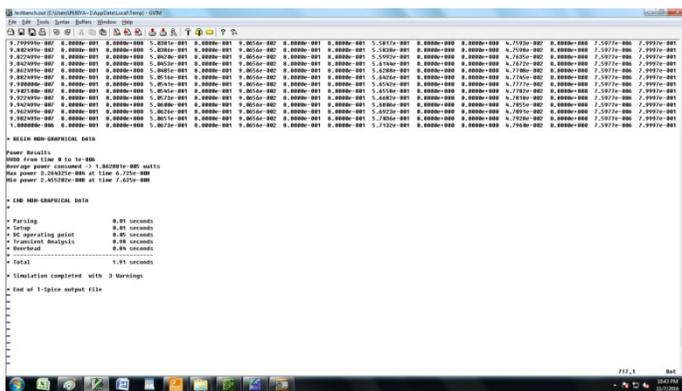
Figure 11: Power report

VI. CONCLUSION

An improvement of the average-8T SRAM architecture is that it does not require a write-back scheme for bit-interleaving, and it displays a competitive subject. Never the less, within the case of an typical-8T SRAM architecture established on a sophisticated technological know-how such as a 22-nm FinFET technology, full-swing LBL can't be done owing to the exchange-off between the readability and the read extend. As a consequence, the gate of the learn buffer cannot be driven by using a full VDD, resulting in a considerably large read delay in a low-voltage neighborhood. Extra, the RBLs in the unselected columns are unnecessarily discharged for the duration of the write operation, resulting within the consumption of a tremendous quantity of dynamic vigour in the write operation. In the proposed differential SRAM, the alternate-off between the read stability and the read delay is eradicated. Accordingly, it may be concluded that the proposed SRAM based on the 22-nm FinFET science displays a greatly smaller read prolong and consumes much less vigour with a somewhat smaller discipline than the usual-8T SRAM.

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